

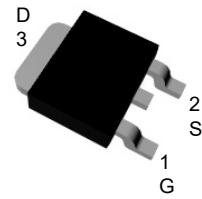
Features

- 650V/8A
 $R_{DS(ON)}=0.5\Omega(\text{typ.})@V_{GS}=10V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

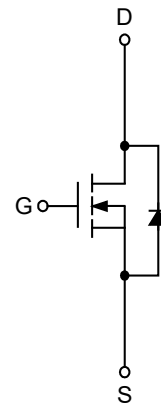
Applications

- AC/DC Power Conversion in Switched Mode Power Supplies (SMPS).
- Uninterruptible Power Supply (UPS).
- Adapter.

Pin Description



TO-252-2



N-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		650	V
V _{GSS}	Gate-Source Voltage		±30	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	8	A
I _D	Continuous Drain Current	T _C =25°C	8	A
		T _C =100°C	6	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	24	
P _D	Maximum Power Dissipation	T _C =25°C	109	W
		T _C =100°C	43	
R _{θJC}	Thermal Resistance-Junction to Case		1.15	°C/W
R _{θJA} ^b	Thermal Resistance-Junction to Ambient		50	°C/W
I _{AS} ^c	Avalanche Current, Single pulse	L=10mH	2	A
E _{AS} ^c	Avalanche Energy, Single pulse	L=10mH	20	mJ

Note a : Pulse width limited by maximum junction temperature.

Note b : Surface Mounted on 1in^2 pad area.

Note c : UIS tested and pulse width limited by maximum junction temperature (initial temperature $T_J=25^{\circ}\text{C}$).

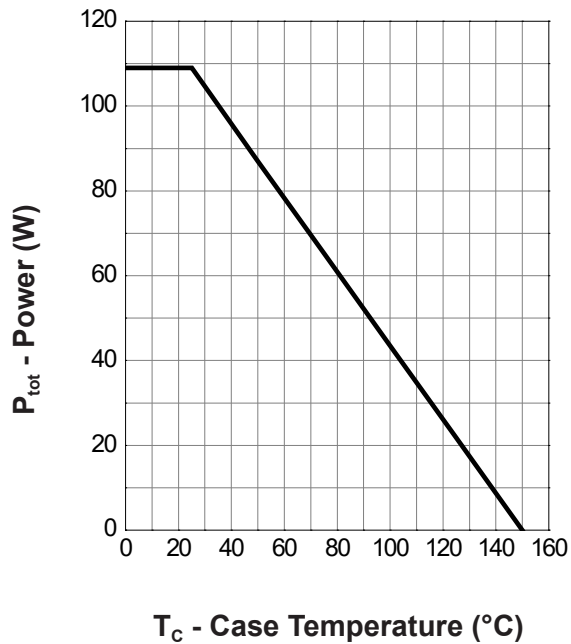
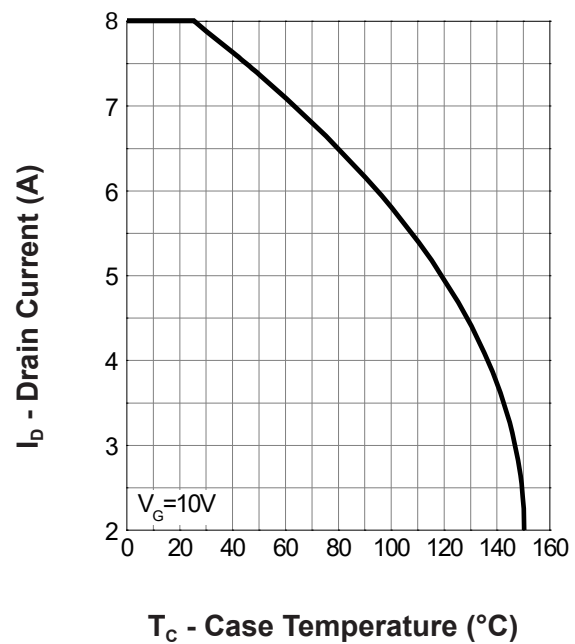
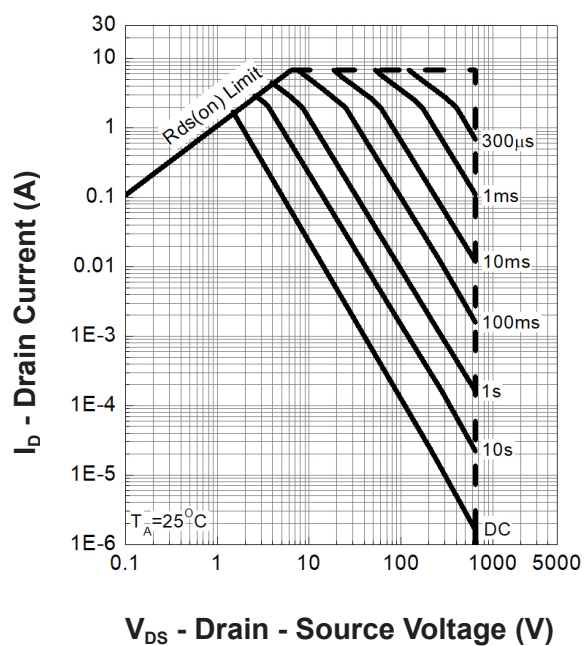
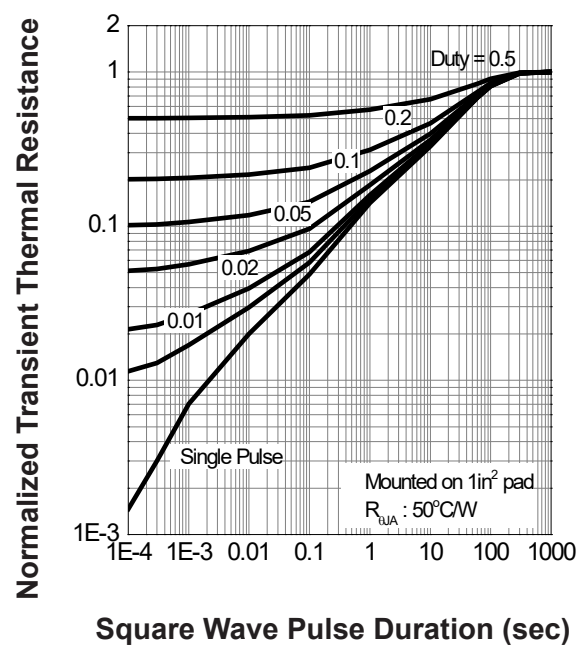
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	650	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =520V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2.5	3.5	4.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±30V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =5.5A	-	0.5	0.6	Ω
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =11A, V _{GS} =0V	-	0.9	1.3	V
t _{rr} ^e	Reverse Recovery Time	I _{SD} =5.5A, dI _{SD} /dt=100A/μs	-	233	-	ns
Q _{rr} ^e	Reverse Recovery Charge		-	2.4	-	μC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	15	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =325V, Frequency=1.0MHz	-	387	-	pF
C _{oss}	Output Capacitance		-	26	-	
C _{rss}	Reverse Transfer Capacitance		-	6	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	17	30	ns
t _r	Turn-on Rise Time		-	16	29	
t _{d(OFF)}	Turn-off Delay Time		-	42	76	
t _f	Turn-off Fall Time		-	71	128	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =325V, V _{GS} =10V, I _{DS} =5.5A	-	18	27	nC
Q _{gs}	Gate-Source Charge		-	4	-	
Q _{gd}	Gate-Drain Charge		-	6.9	-	

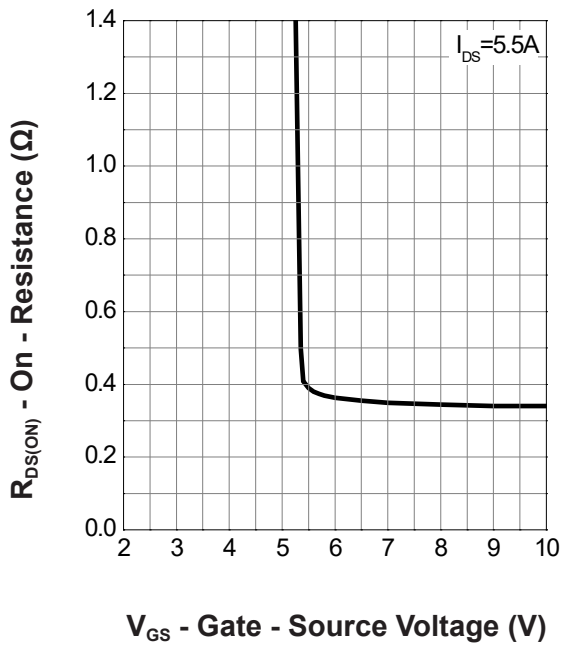
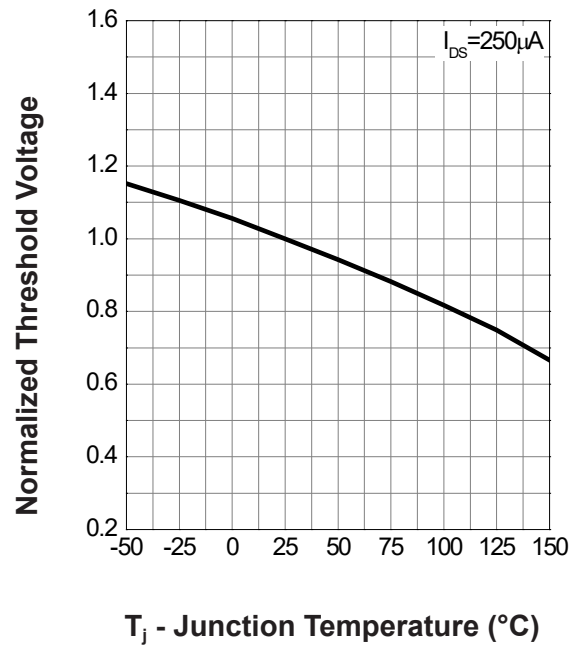
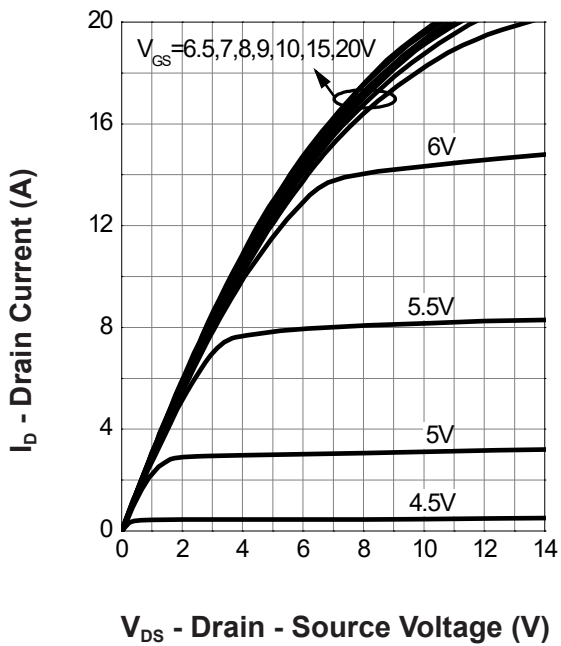
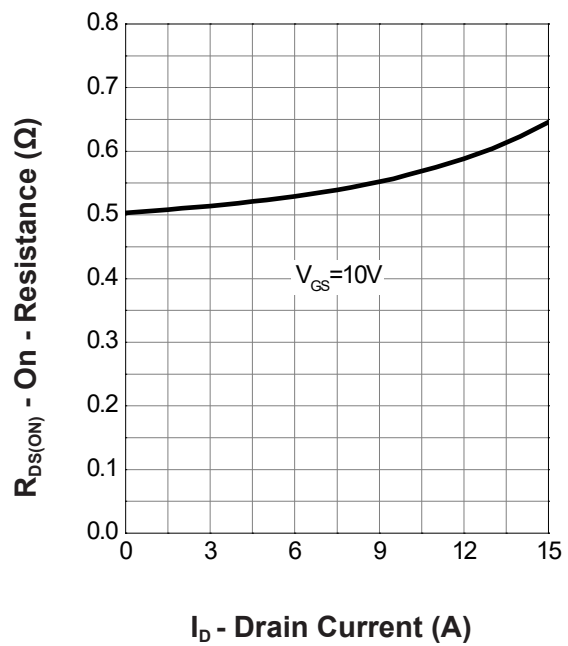
Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note e : Guaranteed by design, not subject to production testing.

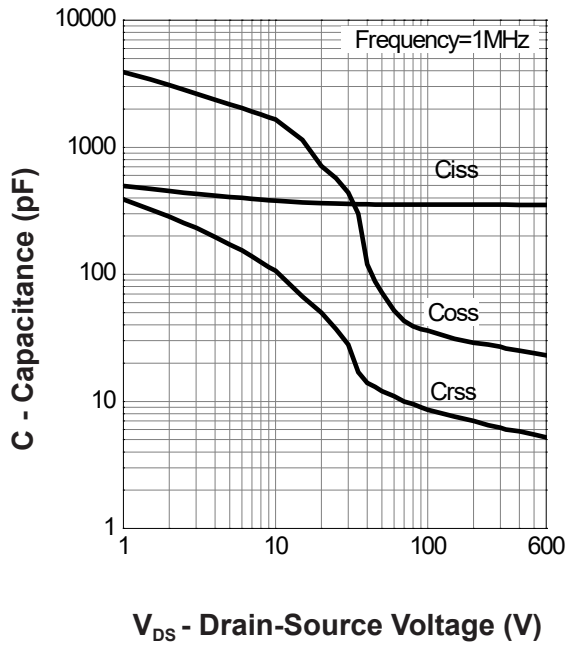
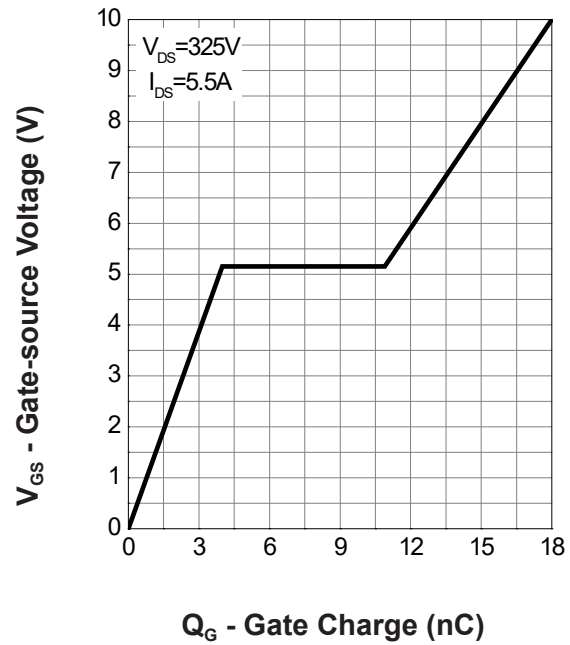
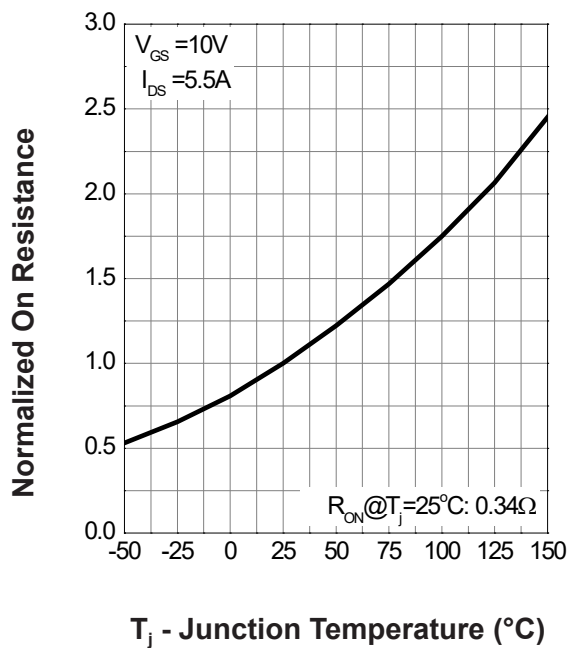
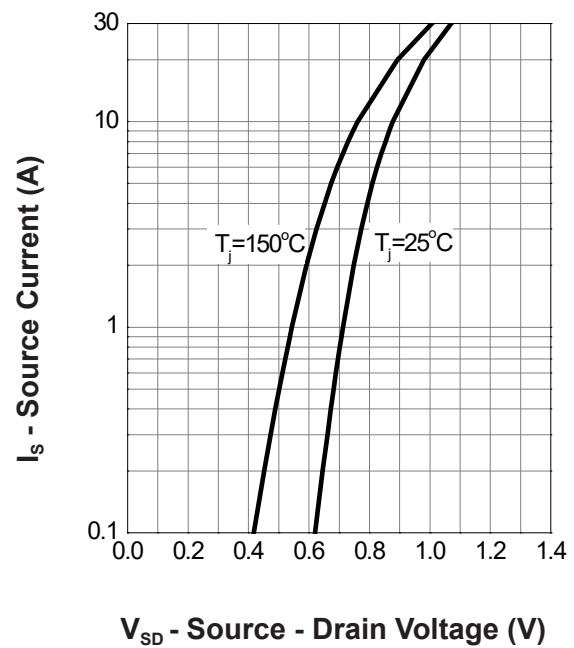
Typical Operating Characteristics

Power Dissipation

Drain Current

Safe Operation Area

Thermal Transient Impedance


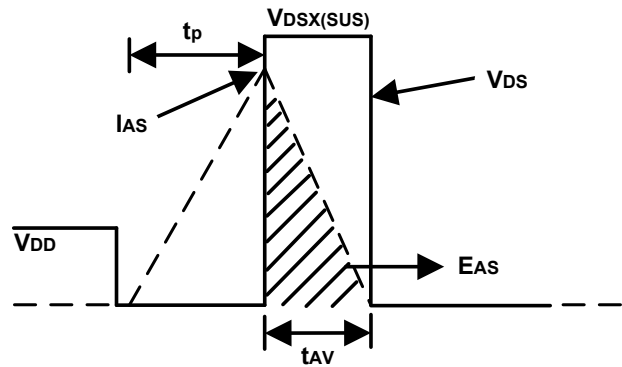
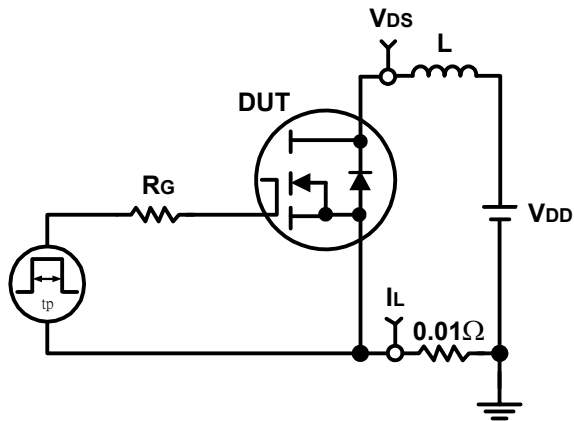
Typical Operating Characteristics(Cont.)

Gate-Source On Resistance

Gate Threshold Voltage

Output Characteristics

Drain-Source On Resistance


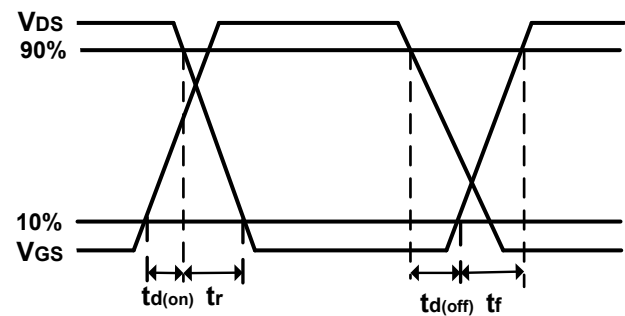
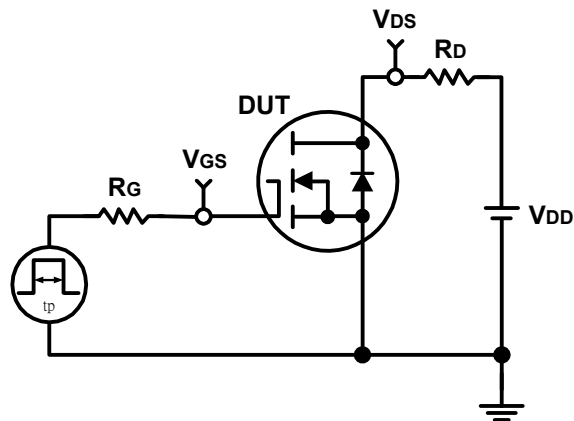
Typical Operating Characteristics(Cont.)

Capacitance

Gate Charge

Drain-Source On Resistance

Source-Drain Diode Forward


Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Package Information

